

# 2SK1304

## Silicon N Channel MOS FET

REJ03G0923-0200  
(Previous: ADE-208-1262)  
Rev.2.00  
Sep 07, 2005

### Application

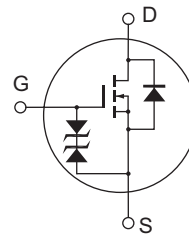
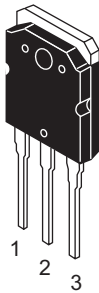
High speed power switching

### Features

- Low on-resistance
- High speed switching
- Low drive current
- 4 V gate drive device
  - Can be driven from 5 V source
- Suitable for motor drive, DC-DC converter, power switch and solenoid drive

### Outline

RENESAS Package code: PRSS0004ZE-A  
(Package name: TO-3P)



1. Gate
2. Drain  
(Flange)
3. Source

## Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	100	V
Gate to source voltage	$V_{GSS}$	$\pm 20$	V
Drain current	$I_D$	40	A
Drain peak current	$I_{D(pulse)}^{*1}$	160	A
Body to drain diode reverse drain current	$I_{DR}$	40	A
Channel dissipation	$P_{ch}^{*2}$	100	W
Channel temperature	$T_{ch}$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

Notes: 1.  $PW \leq 10 \mu s$ , duty cycle  $\leq 1\%$ 2. Value at  $T_C = 25^\circ C$ 

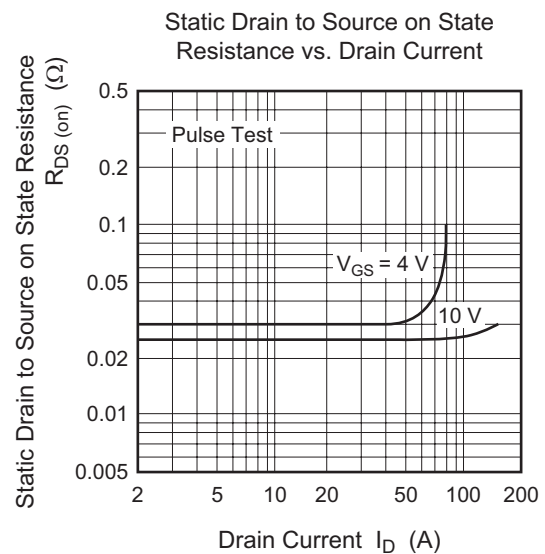
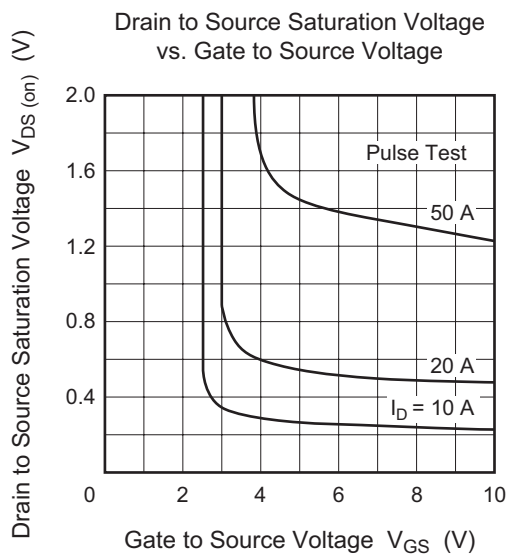
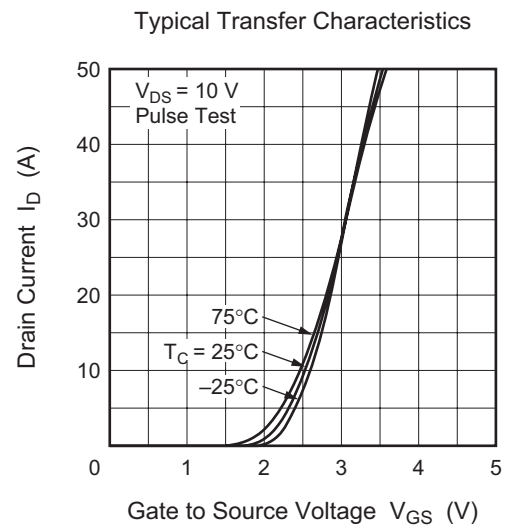
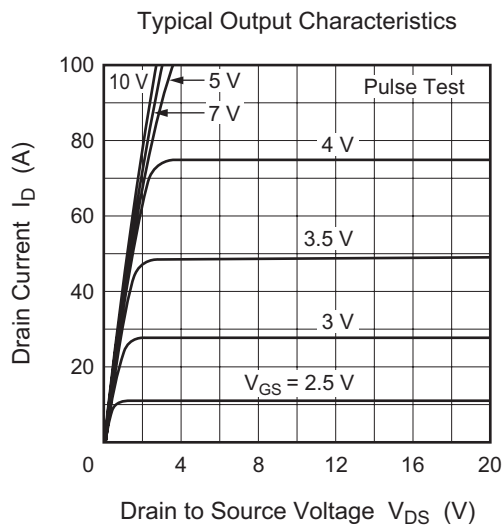
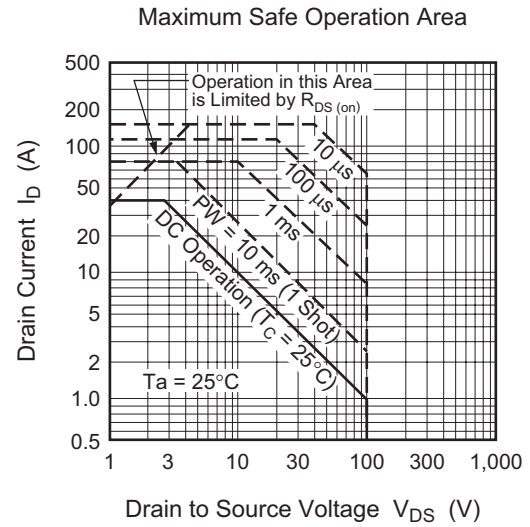
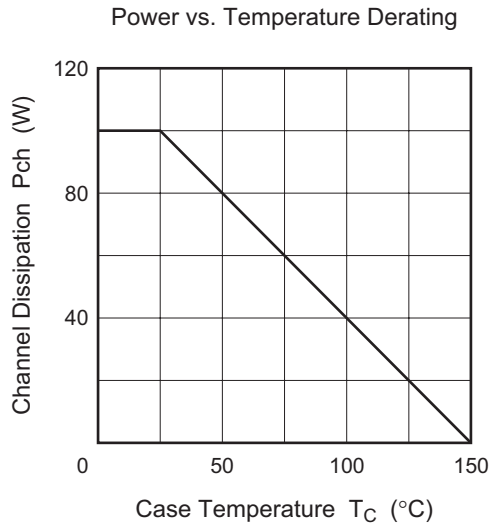
## Electrical Characteristics

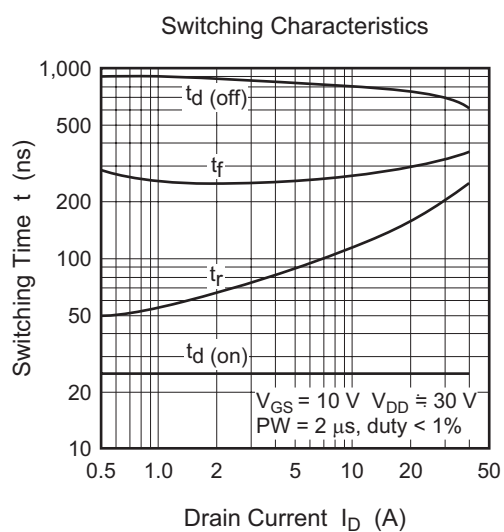
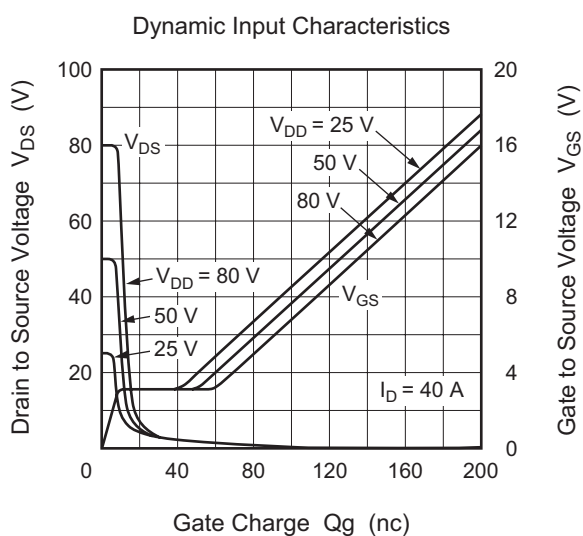
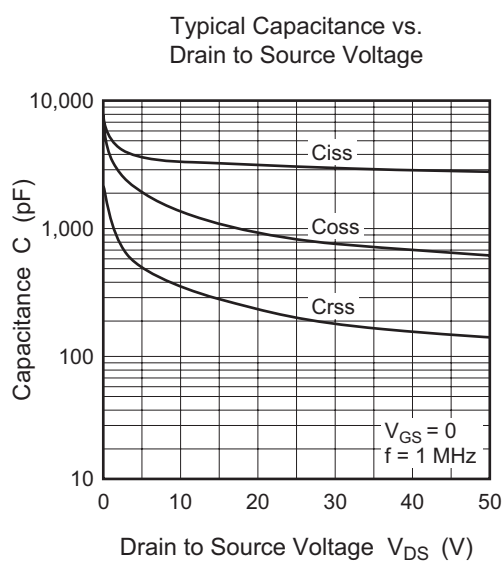
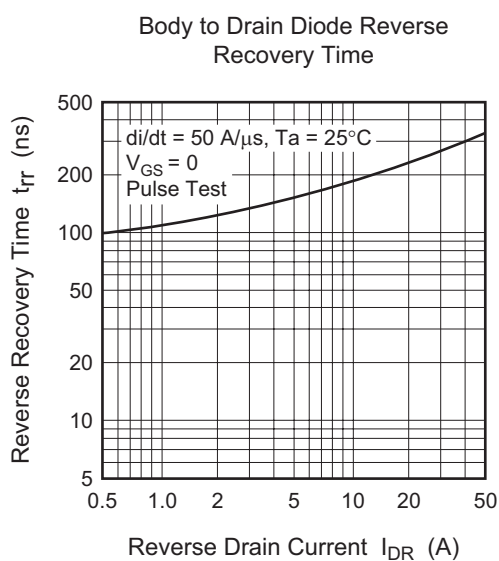
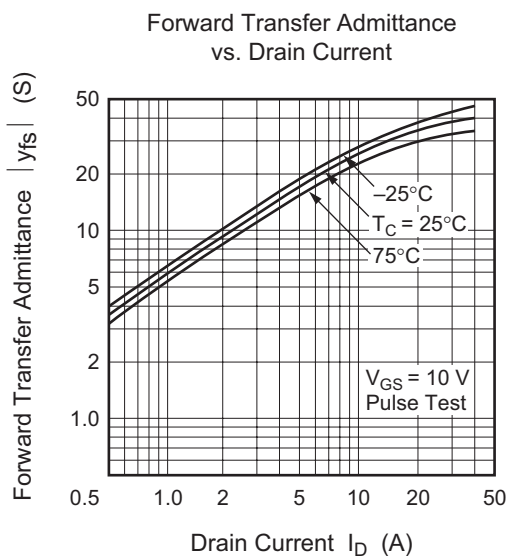
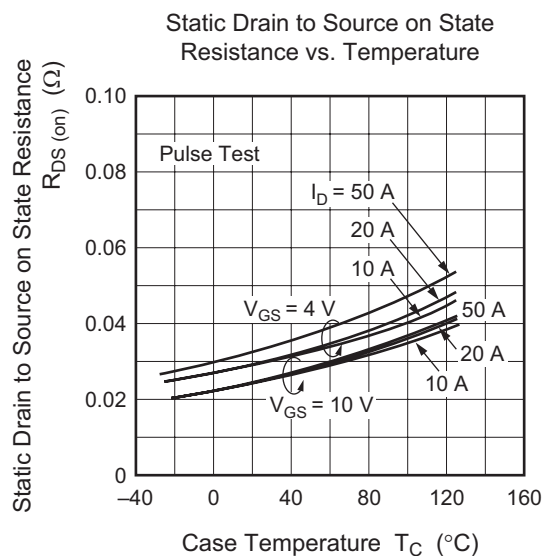
(Ta = 25°C)

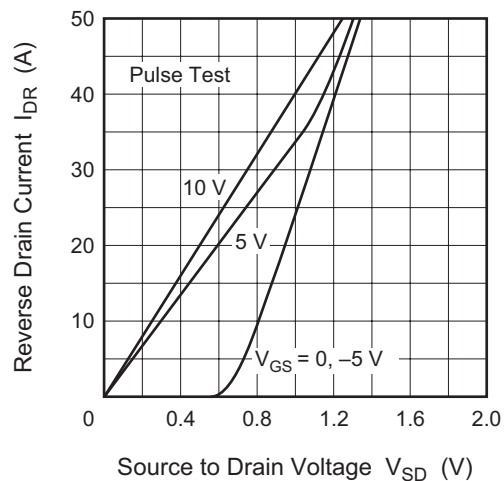
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	100	—	—	V	$I_D = 10 \text{ mA}$ , $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	$\pm 20$	—	—	V	$I_G = \pm 100 \mu A$ , $V_{DS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	$\pm 10$	$\mu A$	$V_{GS} = \pm 16 \text{ V}$ , $V_{DS} = 0$
Zero gate voltage drain current	$I_{DSS}$	—	—	250	$\mu A$	$V_{DS} = 80 \text{ V}$ , $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.0	V	$I_D = 1 \text{ mA}$ , $V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.025	0.03	$\Omega$	$I_D = 20 \text{ A}$ , $V_{GS} = 10 \text{ V}^{*3}$
		—	0.03	0.04	$\Omega$	$I_D = 20 \text{ A}$ , $V_{GS} = 4 \text{ V}^{*3}$
Forward transfer admittance	$ y_{fs} $	22	35	—	S	$I_D = 20 \text{ A}$ , $V_{DS} = 10 \text{ V}^{*3}$
Input capacitance	$C_{iss}$	—	3500	—	pF	$V_{DS} = 10 \text{ V}$ , $V_{GS} = 0$ , $f = 1 \text{ MHz}$
Output capacitance	$C_{oss}$	—	1400	—	pF	
Reverse transfer capacitance	$C_{rss}$	—	340	—	pF	
Turn-on delay time	$t_{d(on)}$	—	25	—	ns	$I_D = 20 \text{ A}$ , $V_{GS} = 10 \text{ V}$ , $R_L = 1.5 \Omega$
Rise time	$t_r$	—	170	—	ns	
Turn-off delay time	$t_{d(off)}$	—	730	—	ns	
Fall time	$t_f$	—	300	—	ns	
Body to drain diode forward voltage	$V_{DF}$	—	1.2	—	V	$I_F = 40 \text{ A}$ , $V_{GS} = 0$
Body to drain diode reverse recovery time	$t_{rr}$	—	300	—	ns	$I_F = 40 \text{ A}$ , $V_{GS} = 0$ , $di_F/dt = 50 \text{ A}/\mu s$

Note: 3. Pulse test

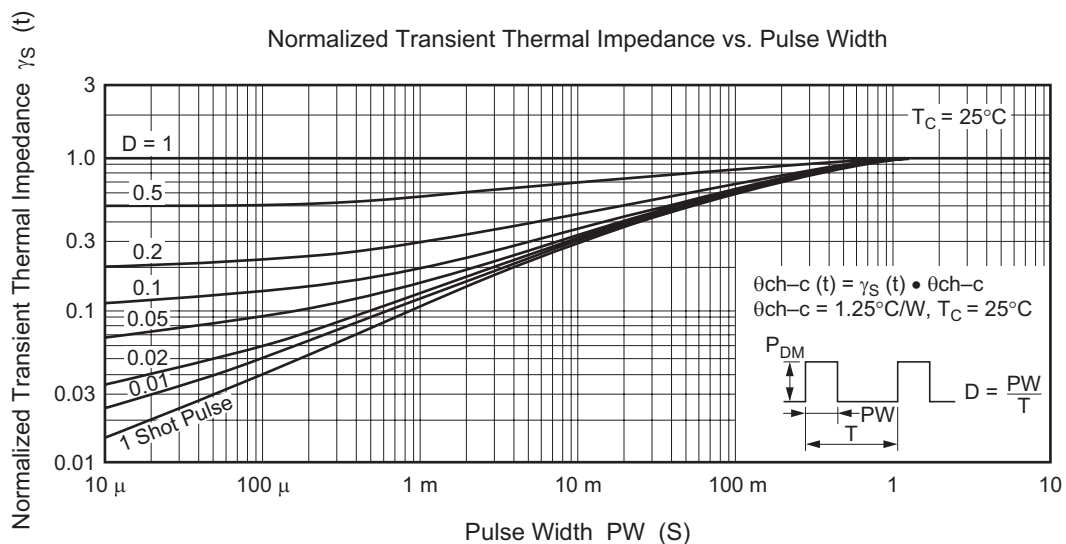
## Main Characteristics



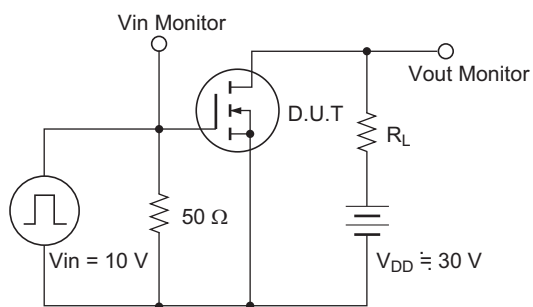


Reverse Drain Current vs.  
Source to Drain Voltage

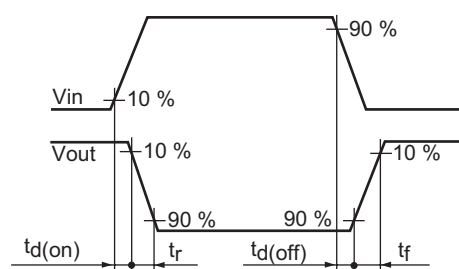
Normalized Transient Thermal Impedance vs. Pulse Width



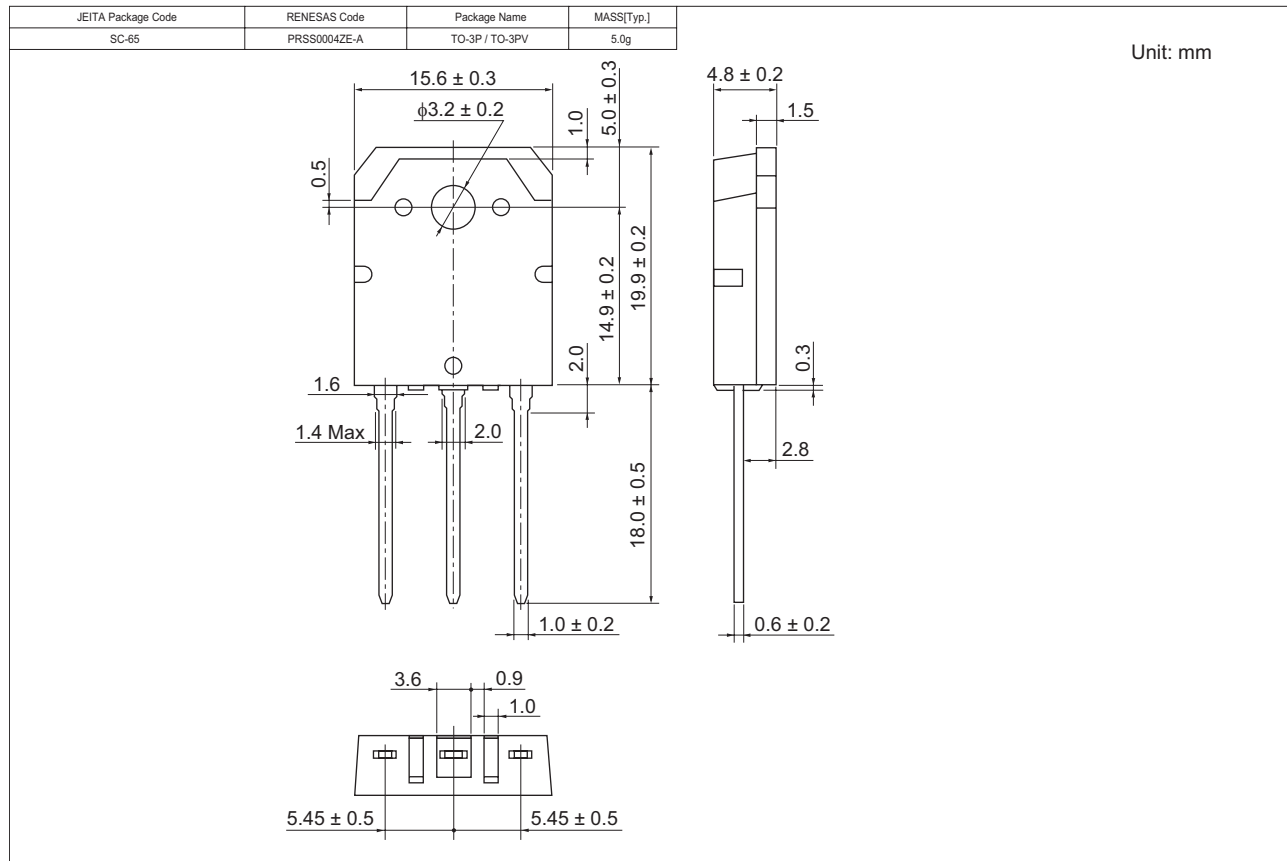
Switching Time Test Circuit



Waveforms



## Package Dimensions



## Ordering Information

Part Name	Quantity	Shipping Container
2SK1304-E	30 pcs	Plastic magazine

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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